



# **Phase Control Thyristor**

DS5833-4 June 2014 (LN31648)

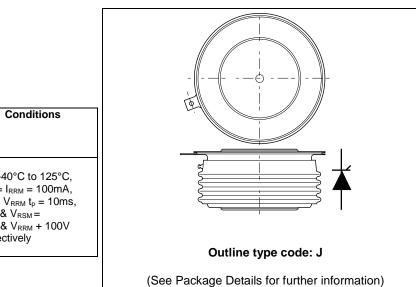
# FEATURES

- Double Side Cooling
- High Surge Capability

### **KEY PARAMETERS**

V <sub>DRM</sub>	8500V
I <sub>T(AV)</sub>	387A
I <sub>TSM</sub>	5250A
dV/dt*	1500V/µs
dl/dt	200A/us

#### \* Higher dV/dt selections available



#### Fig. 1 Package outline

### **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

#### **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages V <sub>DRM</sub> and V <sub>RRM</sub> V	Conditions
DCR390J85* DCR390J80 DCR390J70	8500 8000 7000	$\begin{array}{l} T_{vj} = -40^{\circ}C \ to \ 125^{\circ}C, \\ I_{DRM} = I_{RRM} = 100 mA, \\ V_{DRM}, \ V_{RRM} \ t_p = 10 ms, \\ V_{DSM} \ \& \ V_{RSM} = \\ V_{DRM} \ \& \ V_{RRM} + 100 V \\ respectively \end{array}$

Lower voltage grades available. \*8200V @  $-40^{\circ}$  C, 8500V @  $0^{\circ}$  C

## **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

#### DCR390J85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.



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### **CURRENT RATINGS**

T<sub>case</sub> = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Sid	de Cooled			
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	387	А
I <sub>T(RMS)</sub>	RMS value	-	608	А
Ι <sub>Τ</sub>	Continuous (direct) on-state current	-	583	А

## SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}C$	5.25	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	$V_R = 0$	0.138	MA <sup>2</sup> s

## THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R <sub>th(j-c)</sub>	Thermal resistance – junction to case	Double side cooled	DC	-	0.0379	°C/W
		Single side cooled	Anode DC	-	0.0745	°C/W
			Cathode DC	-	0.0797	°C/W
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink	Clamping force 11.5kN	Double side	-	0.0072	°C/W
		(with mounting compound)	Single side	-	.0144	°C/W
$T_{vj}$	Virtual junction temperature	Blocking V <sub>DRM</sub> / <sub>VRRM</sub>		-	125	°C
T <sub>stg</sub>	Storage temperature range			-55	125	°C
F <sub>m</sub>	Clamping force			10	13	kN

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# **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125°C		-	100	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V <sub>DRM</sub> , T <sub>j</sub> = 125°C, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% $V_{\text{DRM}}$ to 2x $I_{\text{T(AV)}}$	Repetitive 50Hz	-	100	A/µs
		Gate source 30V, $10\Omega$ ,	Non-repetitive	-	200	A/µs
		$t_r < 0.5 \mu s, T_j = 125^{\circ}C$				
V <sub>T(TO)</sub>	Threshold voltage – Low level	50A to 400A at T <sub>case</sub> = 125°C		-	1.162	V
	Threshold voltage – High level	400A to 1600A at T <sub>case</sub> = 125°C		-	1.3063	V
r <sub>T</sub>	On-state slope resistance – Low level	50A to 400A at T <sub>case</sub> = 125°C		-	3.153	mΩ
	On-state slope resistance – High level	400A to 1600A at T <sub>case</sub> = 125°C		-	2.763	mΩ
t <sub>gd</sub>	Delay time	$V_D$ = 67% $V_{DRM}$ , gate source 30V, 10 $\Omega$ t <sub>r</sub> = 0.5µs, T <sub>j</sub> = 25°C		-	3	μs
tq	Turn-off time	$T_j = 125^{\circ}C, V_R = 100V, dI/dt = 5A/\mu s,$		-	1200	μs
		dV <sub>DR</sub> /dt = 20V/µs linear				
Qs	Stored charge	$I_T = 500A, T_j = 125^{\circ}C, dI/dt = 5A/\mu s,$		2000	3000	μC
١L	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
Ι <sub>Η</sub>	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 500A, I_T = 5A$		-	300	mA

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# GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V <sub>GT</sub>	Gate trigger voltage	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	1.5	V
$V_{GD}$	Gate non-trigger voltage	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	0.4	V
I <sub>GT</sub>	Gate trigger current	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	350	mA
I <sub>GD</sub>	Gate non-trigger current	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	15	mA

### CURVES

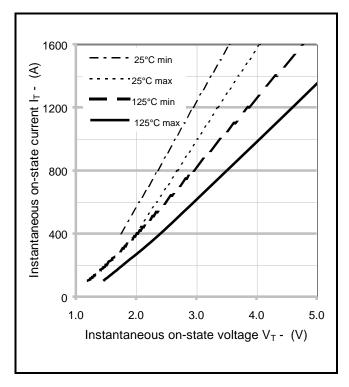


Fig.2 Maximum & minimum on-state characteristics

# V<sub>TM</sub> EQUATION

$$V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$$

Where A = 1.545561B = -0.202735C = 0.001865D = 0.066158

these values are valid for  $T_j$  = 125°C for  $I_T$  50A to 1600A

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### DCR390J85

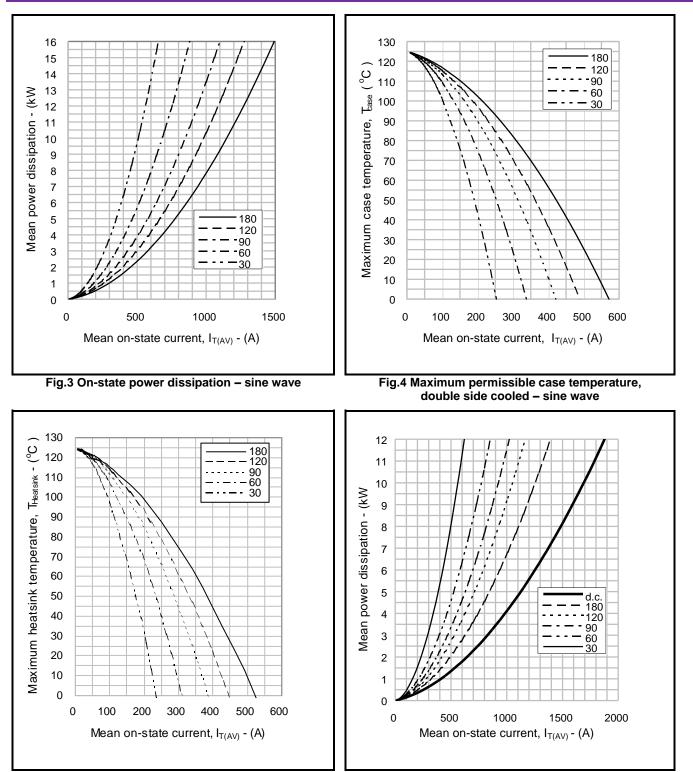


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

Fig.6 On-state power dissipation - rectangular wave

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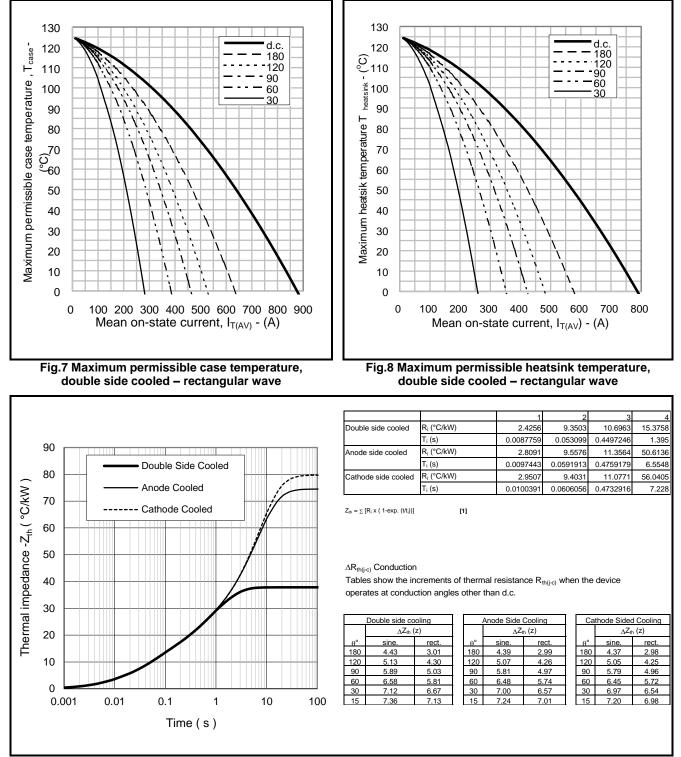


Fig.9 Maximum (limit) transient thermal impedance – junction to case (°C/kW)

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#### DCR390J85

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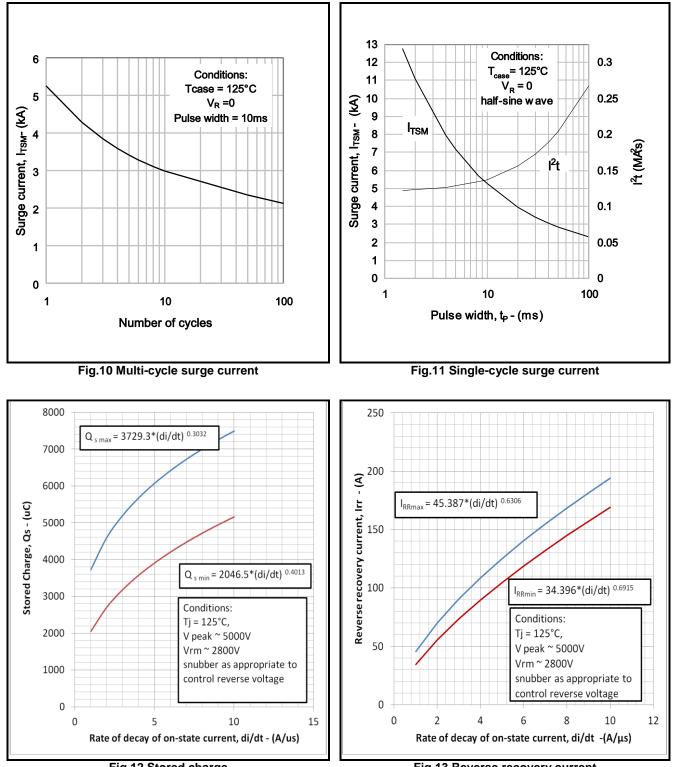
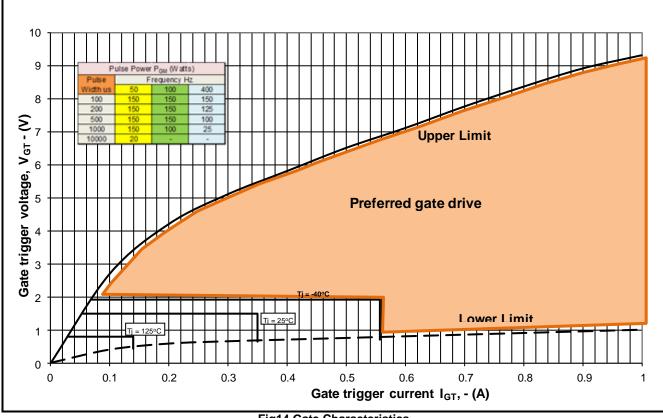


Fig.12 Stored charge

Fig.13 Reverse recovery current



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**Fig14 Gate Characteristics** 

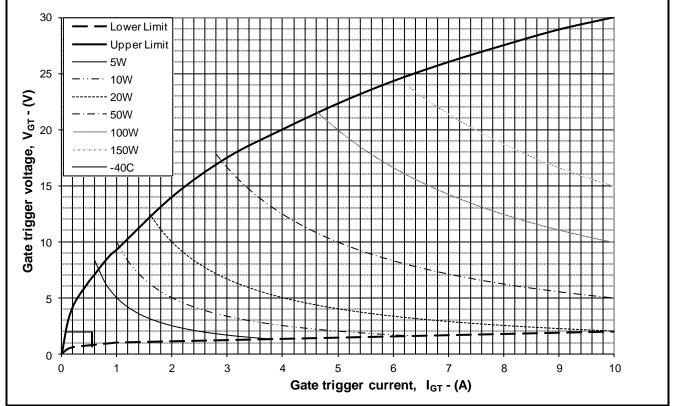


Fig. 15 Gate characteristics



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# PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

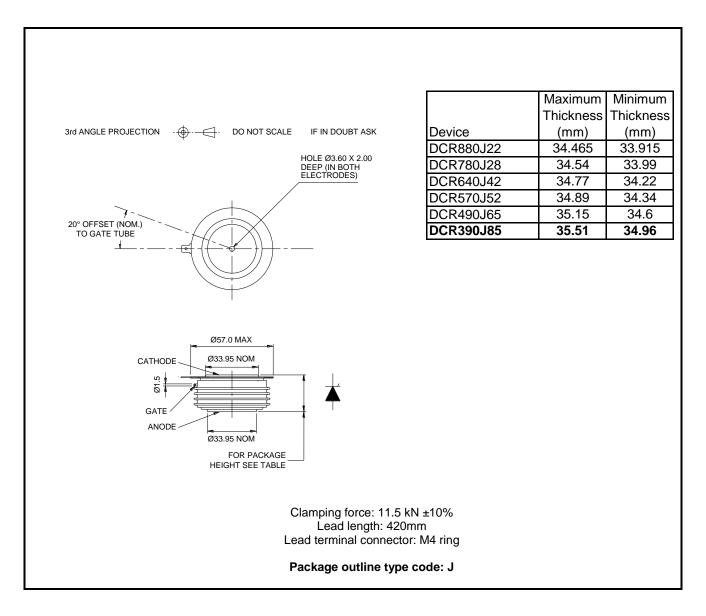


Fig.16 Package outline



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